

Average gate power dissipation ($T_j=150\text{ }^{\circ}\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25\text{ }^{\circ}\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V\ R_L=33\Omega$	- -	MAX.	20	mA
V_{GT}		- -	MAX.	1	V
V_{GD}					

ORDERING INFORMATION

T	08	20	H	-6	A
Triacs	$I_T(RMS):8A$				A:TO-220A(Ins)
	$20:I_{GT1-3} 020 mA$			$6:V_{DRM} / V_{RRM} 1600 V$	
			High junction temperature		

FIG.1: Maximum power dissipation versus RMS on-state current



FIG.2: RMS on-state current versus case temperature

ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T0820H-6A	600	20	TO-220A		

PACKAGE MECHANICAL DATA



